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T. Wada, M. Takeda, T. Yamada and M. Ichimura, Formation of a Ge_xSi_{1-x} alloy layer by high-energy electron-beam irradiation 41/42 (1989) 580

Contacts

M. Murakami, H.J. Kim, Y.-C. Shih, W.H. Price and C.C. Parks, Effects of interfacial microstructure on ohmic contacts to GaAs 41/42 (1989) 195

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Diamond

J.-S. Ma, H. Kawarada, T. Yonehara, J.-I. Suzuki, J. Wei, Y. Yokota, H. Mori, H. Fujita and A. Hiraki, Interfacial structures and selective growth of diamond particles formed by plasma-assisted CVD 41/42 (1989) 572

Diffusion

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A. Förster, J.M. Layet and H. Lüth, Evaluation of dopant profiles and diffusion constants by means of electron energy loss spectroscopy 41/42 (1989) 306
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A. Förster, J.M. Layet and H. Lüth, Evaluation of dopant profiles and diffusion constants by means of electron energy loss spectroscopy 41/42 (1989) 306
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K. Hirose, H. Tsuda and T. Mizutani, Control of the Al/GaAs Schottky barrier height using a rare-earth metal interlayer 41/42 (1989) 174
T. Arakawa, H. Baba and G. Adachi, Deep level transient spectroscopic studies of the perovskite oxides as gas sensor material 41/42 (1989) 212
N. Fujimura and T. Ito, $TiSi_2$ formation at the Ti-rich TiN_x/Si interface 41/42 (1989) 272
S. Ogawa, T. Yoshida, T. Kouzaki, S. Okuda and K. Tsukamoto, Thermal instability of the $TiSi_2$/Si structure: impurity effects 41/42 (1989) 290
H. Hasegawa, H. Ohno, H. Ishii, T. Haga, Y. Abe and H. Takahashi, Origin and properties of interface states at insulator–semiconductor and semiconductor–semiconductor interfaces of compound semiconductors 41/42 (1989) 372

A.S. Barrière, G. Couturier, H. Guegan, T. Séguelong, A. Thabti, P. Alnot and J. Chazelas, Interface GaAs – gallium fluoride thin film grown by fluorination. Electrical behaviour of the obtained MIS fluorinated GaAs structures 41/42 (1989) 383

T. Saitoh, H. Hasegawa, S. Konishi and H. Ohno, A computer simulation of the recombination process at compound semiconductor surfaces and hetero-interfaces 41/42 (1989) 402

Y. Yasuda, S. Zaima and M. Sakashita, Studies on charge trapping and interface state generation in MOS capacitors at low temperatures 41/42 (1989) 420

S. Zaima, T. Maruyama and Y. Yasuda, Piezoresistance in n-channel inversion layers of Si MOSFET's 41/42 (1989) 433

K. Kamimura, Y. Takase, Y. Onuma and A. Kunioka, Surface nitridation of InP with a N_2 plasma 41/42 (1989) 443

S. Fujieda, K. Akimoto, I. Hirosawa, Y. Mochizuki, J. Mizuki, Y. Matsumoto and J. Matsui, Electrical properties and structures of the MOCVD-AlN/GaAs interface 41/42 (1989) 516

T. Aoyama, T. Sugi and T. Ito, Determination of band line-up in β-SiC/Si heterojunction for Si-HBT's 41/42 (1989) 584

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A. Ichimiya, S. Kohmoto, T. Fujii and Y. Horio, RHEED intensity analysis of Si(111)$\sqrt{3} \times \sqrt{3}$-Ag structure 41/42 (1989) 82

T. Urano, M. Kaburagi, S. Hongo and T. Kanaji, LEED I–V curve analysis for the structure of iron films on Si(111) surfaces 41/42 (1989) 103

S. Kohmoto, S. Mizuno and A. Ichimiya, RHEED intensity analysis of Li/Si(111) structures 41/42 (1989) 107

S.-T. Li, S. Hasegawa, N. Yamashita and H. Nakashima, Initial stages of aluminum epitaxy on the Si(111)-$\sqrt{3} \times \sqrt{3}$-Al surface studied by electron-energy-loss spectroscopy 41/42 (1989) 118

N. Esser, M. Hünermann, U. Resch, D. Spaltmann, J. Geurts, D.R.T. Zahn, W. Richter and R.H. Williams, Bismuth on GaAs(110): characterisation of growth mode and Schottky barrier formation at low and room temperature 41/42 (1989) 169

M. Renda and K. Morita, Epitaxial growth of a mono-crystalline metastable AuIn layer at the Au/InP(001) interface 41/42 (1989) 216

J. Falta, M. Horn and M. Henzler, SPA-LEED studies of defects in thin epitaxial $NiSi_2$ layers on Si(111) 41/42 (1989) 230

N. Cherief, R. Cinti, M. De Crescenzi, J. Derrien, T.A. Nguyen Tan and J.Y. Veuillen, Heteroepitaxy of metallic and semiconducting silicides on silicon 41/42 (1989) 241

I. Yamada, Interfacial structure of ICB epitaxially deposited Al(110) bicrystal films on Si(100) substrates 41/42 (1989) 253

M. Itoh, M. Kinoshita, T. Ajioka, M. Itoh and T. Inada, Crystalline quality of heteroepitaxial silicon on epitaxial $NiSi_2$/Si(100) 41/42 (1989) 262

N. Fujimura and T. Ito, $TiSi_2$ formation at the Ti-rich TiN_x/Si interface 41/42 (1989) 272

N. Fujimura, S. Tachibana and T. Ito, Characterization of Si-rich WSi_x on Si 41/42 (1989) 286

K. Takayanagi, Y. Tanishiro, T. Ishitsuka and K. Akiyama, In-situ UHV electron microscope study of metal–silicon surfaces 41/42 (1989) 337

A. Koma, K. Saiki and Y. Sato, Heteroepitaxy of a two-dimensional material on a three-dimensional material 41/42 (1989) 451

M. Yano, M. Ashida, Y. Iwai and M. Inoue, Characteristic properties of III–V_A/III–V_B heterointerfaces grown by molecular beam epitaxy 41/42 (1989) 457

S. Tatarenko, J. Cibert, Y. Gobil, G. Feuillet, K. Saminadayar, A.C. Chami and E. Ligeon, RHEED, XPS, HRTEM and channeling studies of molecular beam epitaxy growth of CdTe on (001) GaAs 41/42 (1989) 470

T. Nomura, K. Wakatuki, M. Miyao and M. Hagino, Characterization of the GaAs buffer layer grown on GaP by MBE for the two-step growth method 41/42 (1989) 512

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Electron emission

M.H. Hecht, L.D. Bell and W.J. Kaiser, Ballistic-electron-emission microscopy of subsurface defects at the Au–GaAs(100) interface 41/42 (1989) 17

Electron energy loss spectroscopy

S.-T. Li, S. Hasegawa, N. Yamashita and H. Nakashima, Initial stages of aluminum epitaxy on the Si(111)-$\sqrt{3} \times \sqrt{3}$-Al surface studied by electron-energy-loss spectroscopy 41/42 (1989) 118
X.M. Ding, G.S. Dong, X.K. Lu, H.Y. Xiao, P. Chen and X. Wang, Application of HREELS to Al/GaAs and Al/GaP interfaces 41/42 (1989) 123
R. Sporken, P.A. Thiry, P. Xhonneux, R. Caudano and J.P. Delrue, Spectroscopic study of metal/semimetal and metal/semiconductor interfaces 41/42 (1989) 201
A. Förster, J.M. Layet and H. Lüth, Evaluation of dopant profiles and diffusion constants by means of electron energy loss spectroscopy 41/42 (1989) 306
C. Tatsuyama, T. Tanbo and N. Nakayama, Heteroepitaxy between layered semiconductors GaSe and InSe 41/42 (1989) 539
H.C. Lee, H. Ishiwara, S. Furukawa, K. Saiki and A. Koma, Distribution of interfacial As atoms in the electron-beam exposure and epitaxy (EBE-epitaxy) technique for growing GaAs films on CaF_2/Si(111) structures 41/42 (1989) 553

Electron microscopy

M. Murakami, H.J. Kim, Y.-C. Shih, W.H. Price and C.C. Parks, Effects of interfacial microstructure on ohmic contacts to GaAs 41/42 (1989) 195
R.T. Tung and F. Schrey, Epitaxial $CoSi_2$/Si(111) interfaces 41/42 (1989) 223
N. Cherief, R. Cinti, M. De Crescenzi, J. Derrien, T.A. Nguyen Tan and J.Y. Veuillen, Heteroepitaxy of metallic and semiconducting silicides on silicon 41/42 (1989) 241
I. Yamada, Interfacial structure of ICB epitaxially deposited Al(110) bicrystal films on Si(100) substrates 41/42 (1989) 253
M. Itoh, M. Kinoshita, T. Ajioka, M. Itoh and T. Inada, Crystalline quality of heteroepitaxial silicon on epitaxial $NiSi_2$/Si(100) 41/42 (1989) 262
N. Fujimura, S. Tachibana and T. Ito, Characterization of Si-rich WSi_x on Si 41/42 (1989) 286
S. Ogawa, T. Yoshida, T. Kouzaki, S. Okuda and K. Tsukamoto, Thermal instability of the $TiSi_2$/Si structure: impurity effects 41/42 (1989) 290
T. Ito, A. Yamama, A. Hiraki and M. Satou, Silicidation of porous silicon and its application for the fabrication of a buried metal layer 41/42 (1989) 301
K. Takayanagi, Y. Tanishiro, T. Ishitsuka and K. Akiyama, In-situ UHV electron microscope study of metal–silicon surfaces 41/42 (1989) 337
H. Akatsu and I. Ohdomari, HRTEM observation of the Si/SiO_2 interface 41/42 (1989) 357
A. Ourmazd, P.H. Fuoss, J. Bevk and J.F. Morar, The Si(001)/SiO_2 interface 41/42 (1989) 365
H. Hasegawa, H. Ohno, H. Ishii, T. Haga, Y. Abe and H. Takahashi, Origin and properties of interface states at insulator–semiconductor and semiconductor–semiconductor interfaces of compound semiconductors 41/42 (1989) 372
A.S. Barrière, G. Couturier, H. Guegan, T. Séguelong, A. Thabti, P. Alnot and J. Chazelas, Interface GaAs – gallium fluoride thin film grown by fluorination. Electrical behaviour of the obtained MIS fluorinated GaAs structures 41/42 (1989) 383
S. Nadahara, J. Shiozawa, K. Imai, K. Suguro and K. Yamabe, Protuberance growth at polysilicon surfaces during oxidation 41/42 (1989) 425
S. Tatarenko, J. Cibert, Y. Gobil, G. Feuillet, K. Saminadayar, A.C. Chami and E. Ligeon, RHEED, XPS, HRTEM and channeling studies of molecular beam epitaxy growth of CdTe on (001) GaAs 41/42 (1989) 470
T. Sasaki, T. Matsuoka and A. Katsui, MOVPE-grown GaN on polar planes of 6H-SiC 41/42 (1989) 504
J.-S. Ma, H. Kawarada, T. Yonehara, J.-I. Suzuki, J. Wei, Y. Yokota, H. Mori, H. Fujita and A. Hiraki, Interfacial structures and selective growth of diamond particles formed by plasma-assisted CVD 41/42 (1989) 572

H. Horikawa, M. Akiyama, S. Onozawa, Y. Kawai and M. Sakuta, Interfacial layers of InP/Si heteroepitaxy 41/42 (1989) 598
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R.T. Tung and F. Schrey, Epitaxial $CoSi_2$/Si(111) interfaces 41/42 (1989) 223
I. Yamada, Interfacial structure of ICB epitaxially deposited Al(110) bicrystal films on Si(100) substrates 41/42 (1989) 253
M. Itoh, M. Kinoshita, T. Ajioka, M. Itoh and T. Inada, Crystalline quality of heteroepitaxial silicon on epitaxial $NiSi_2$/Si(100) 41/42 (1989) 262
S. Hongo, Y. Kataoka, T. Urano and T. Kanaji, Evaluation by resonant light scattering of ZnTe epitaxial layer deposited on GaAs 41/42 (1989) 522
C. Tatsuyama, T. Tanbo and N. Nakayama, Heteroepitaxy between layered semiconductors GaSe and InSe 41/42 (1989) 539
H. Kumomi, T. Yonehara, Y. Nishigaki and N. Sato, Selective nucleation based epitaxy (Sentaxy). Investigation of initial nucleation stages 41/42 (1989) 638

Etching

T. Hattori, H. Yamagishi, N. Koike, K. Imai and K. Yamabe, Structural studies of ultrathin silicon oxides and their interfaces by XPS 41/42 (1989) 416

Gallium arsenide

W.E. Spicer, R. Cao, K. Miyano, T. Kendelewicz, I. Lindau, E. Weber, Z. Liliental-Weber and N. Newman, From synchrotron radiation to I–V measurements of GaAs Schottky barrier formation 41/42 (1989) 1
X.M. Ding, G.S. Dong, X.K. Lu, H.Y. Xiao, P. Chen and X. Wang, Application of HREELS to Al/GaAs and Al/GaP interfaces 41/42 (1989) 123
R. Ludeke, A. Taleb-Ibrahimi and G. Jezequel, Delocalization of defects: a new model for the Schottky barrier 41/42 (1989) 151
N. Esser, M. Hünermann, U. Resch, D. Spaltmann, J. Geurts, D.R.T. Zahn, W. Richter and R.H. Williams, Bismuth on GaAs(110): characterisation of growth mode and Schottky barrier formation at low and room temperature 41/42 (1989) 169
J. Christen, M. Grundmann and D. Bimberg, Direct imaging and theoretical modelling of the atomistic morphological and chemical structure of semiconductor heterointerfaces 41/42 (1989) 329
R. Haight and J.A. Silberman, Surface intervalley scattering on GaAs(110) studied with picosecond laser photoemission 41/42 (1989) 487
T. Takeuchi, C. Maezawa, T. Nomura, K. Ishikawa, M. Miyao and M. Hagino, Raman study of strain distribution in interface region of GaAs/GaP heteroepitaxial layers grown by MBE 41/42 (1989) 530
H.C. Lee, H. Ishiwara, S. Furukawa, K. Saiki and A. Koma, Distribution of interfacial As atoms in the electron-beam exposure and epitaxy (EBE-epitaxy) technique for growing GaAs films on CaF_2/Si(111) structures 41/42 (1989) 553
K. Maehashi, S. Hasegawa and H. Nakashima, Atomic rearrangement during the initial stages of GaAs growth on Si(111)($\sqrt{3} \times \sqrt{3}$)–Ga surface 41/42 (1989) 567

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X.M. Ding, G.S. Dong, X.K. Lu, H.Y. Xiao, P. Chen and X. Wang, Application of HREELS to Al/GaAs and Al/GaP interfaces 41/42 (1989) 123

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Germanium

E. Vlieg and J.F. van der Veen, X-ray scattering studies of semiconductor interfaces: atomic structure and morphology 41/42 (1989) 62

J.F. Morar, U.O. Karlsson, R.I.G. Uhrberg, J. Kanski, P.O. Nilsson and H. Qu, Angle-resolved photoemission study of the As/Ge(100) interface 41/42 (1989) 312

Gold

R.S. Williams, R.S. Daley, J.H. Huang and R.M. Charatan, Initial stages of metal/semiconductor interface formation: Au and Ag on Si(111) 41/42 (1989) 70

Halides

H.C. Lee, H. Ishiwara, S. Furukawa, K. Saiki and A. Koma, Distribution of interfacial As atoms in the electron-beam exposure and epitaxy (EBE-epitaxy) technique for growing GaAs films on CaF_2/Si(111) structures 41/42 (1989) 553

Heterostructures

M. Iwami, M. Kusaka, M. Hirai and H. Nakamura, A new non-destructive analysis of semiconductor heterojunctions with very thin surface layers: an application of soft X-ray spectroscopy to Si-compound (film)/Si (substrate) 41/42 (1989) 57

D.W. Niles, M. Tang, J. McKinley, R. Zanoni and G. Margaritondo, From heterojunction interfaces to metal–semiconductor interfaces 41/42 (1989) 139

F. Flores, A. Muñoz and J.C. Durán, Semiconductor interface formation: the role of the induced density of interface states 41/42 (1989) 144

N. Cherief, R. Cinti, M. De Crescenzi, J. Derrien, T.A. Nguyen Tan and J.Y. Veuillen, Heteroepitaxy of metallic and semiconducting silicides on silicon 41/42 (1989) 241

J.L. Freeouf, The analysis of complex samples by spectroscopic ellipsometry 41/42 (1989) 323

A. Koma, K. Saiki and Y. Sato, Heteroepitaxy of a two-dimensional material on a three-dimensional material 41/42 (1989) 451

M. Yano, M. Ashida, Y. Iwai and M. Inoue, Characteristic properties of III–V_A/III–V_B heterointerfaces grown by molecular beam epitaxy 41/42 (1989) 457

C. López, J. Sánchez-Dehesa, F. Meseguer, F. Borondo and K. Ploog, Electronic structure of modulation n-doped multiple quantum well 41/42 (1989) 464

K. Kanamoto, K. Fujiwara, Y. Tokuda, N. Tsukada, M. Ishii and T. Nakayama, Photoluminescence line shape due to arrayed steps at the interfaces of GaAs/AlGaAs single quantum wells grown on vicinal surfaces by molecular beam epitaxy 41/42 (1989) 526

T. Takeuchi, C. Maezawa, T. Nomura, K. Ishikawa, M. Miyao and M. Hagino, Raman study of strain distribution in interface region of GaAs/GaP heteroepitaxial layers grown by MBE 41/42 (1989) 530

S. Hayashi, T. Sakamoto, S. Fujita and S. Fujita, Strained-layer superlattice buffers for high-quality heteroepilayers of ZnSe on GaAs 41/42 (1989) 534

C. Tatsuyama, T. Tanbo and N. Nakayama, Heteroepitaxy between layered semiconductors GaSe and InSe 41/42 (1989) 539

Y. Kanemitsu and S. Imamura, Charge transport and trapping at the interface in two-layer organic photoconductors 41/42 (1989) 544

H.C. Lee, H. Ishiwara, S. Furukawa, K. Saiki and A. Koma, Distribution of interfacial As atoms in the electron-beam exposure and epitaxy (EBE-epitaxy) technique for growing GaAs films on CaF_2/Si(111) structures 41/42 (1989) 553

K. Maehashi, S. Hasegawa and H. Nakashima, Atomic rearrangement during the initial stages of GaAs growth on Si(111)($\sqrt{3} \times \sqrt{3}$)–Ga surface 41/42 (1989) 567

T. Wada, M. Takeda, T. Yamada and M. Ichimura, Formation of a Ge_xSi_{1-x} alloy layer by high-energy electron-beam irradiation 41/42 (1989) 580

K. Iizuka, T. Yoshida, M. Hasobe, I. Matsuda and T. Suzuki, Raman study of the stress in MBE-grown Al_x-$Ga_{1-x}As$ on Si 41/42 (1989) 587

Indium arsenide

J. Christen, M. Grundmann and D. Bimberg, Direct imaging and theoretical modelling of the atomistic morphological and chemical structure of semiconductor heterointerfaces 41/42 (1989) 329

Indium phosphide

D.R.T. Zahn, W. Richter, A.B. McLean, R.H. Williams, C. Stephens, I.T. McGovern, R. Cimino, W. Braun and N. Esser, Temperature effects on the formation of the Sb/InP(110) interface 41/42 (1989) 179

H. Ishii, H. Hasegawa, A. Ishii and H. Ohno, X-ray photo-electron spectroscopy analysis of InP insulator–semiconductor structures prepared by anodic oxidation 41/42 (1989) 390

K. Kamimura, Y. Takase, Y. Onuma and A. Kunioka, Surface nitridation of InP with a N_2 plasma 41/42 (1989) 443

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K. Matsuo and K. Nakano, Characterization of semiconductor oxides by IR diffuse reflectance spectroscopy 41/42 (1989) 53

D.R.T. Zahn, W. Richter, T. Eickhoff, J. Geurts, T.D. Golding, J.H. Dinan, K.J. Mackey and R.H. Williams, The influence of Cd overpressure in the molecular beam epitaxy of InSb/CdTe heterostructures: a combined Raman and infrared spectroscopy study 41/42 (1989) 497

Y. Kato, T. Ito and A. Hiraki, Low temperature oxidation of crystalline porous silicon 41/42 (1989) 614

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F.J. Himpsel, T.F. Heinz, A.B. McLean and E. Palange, Bonding at silicon/insulator interfaces 41/42 (1989) 346

A. Ourmazd, P.H. Fuoss, J. Bevk and J.F. Morar, The Si(001)/SiO_2 interface 41/42 (1989) 365

H. Hasegawa, H. Ohno, H. Ishii, T. Haga, Y. Abe and H. Takahashi, Origin and properties of interface states at insulator–semiconductor and semiconductor–semiconductor interfaces of compound semiconductors 41/42 (1989) 372

A.S. Barrière, G. Couturier, H. Guegan, T. Séguelong, A. Thabti, P. Alnot and J. Chazelas, Interface GaAs – gallium fluoride thin film grown by fluorination. Electrical behaviour of the obtained MIS fluorinated GaAs structures 41/42 (1989) 383

H. Ishii, H. Hasegawa, A. Ishii and H. Ohno, X-ray photo-electron spectroscopy analysis of InP insulator–semiconductor structures prepared by anodic oxidation 41/42 (1989) 390

P. Soukiassian, H.I. Starnberg and T. Kendelewicz, Insulator–semiconductor interface formation by electronic promotion using alkali metal and removal of the catalyst 41/42 (1989) 395

H. Miyatake, Y. Yamaguchi, Y. Mashiko, T. Nishimura and H. Koyama, Microstructure of high temperature annealed SIMOX wafer 41/42 (1989) 643

Y. Yamada Maruo, M. Oshima, T. Waho, T. Kawamura, S. Maeyama and T. Miyahara, Photoemission studies of bonding properties at the MBE-grown CaF_2/GaAs interface 41/42 (1989) 647

Interfaces

M.H. Hecht, L.D. Bell and W.J. Kaiser, Ballistic-electron-emission microscopy of subsurface defects at the Au–GaAs(100) interface 41/42 (1989) 17

G. Le Lay, K. Hricovini and J.E. Bonnet, Synchrotron radiation investigation and surface spectroscopy studies of prototypical systems: lead–semiconductor interfaces 41/42 (1989) 25

X.M. Ding, G.S. Dong, X.K. Lu, H.Y. Xiao, P. Chen and X. Wang, Application of HREELS to Al/GaAs and Al/GaP interfaces 41/42 (1989) 123

H. Fujitani and S. Asano, Electronic structure of Si/disilicide interfaces 41/42 (1989) 164

D.R.T. Zahn, W. Richter, A.B. McLean, R.H. Williams, C. Stephens, I.T. McGovern, R. Cimino, W. Braun and N. Esser, Temperature effects on the formation of the Sb/InP(110) interface 41/42 (1989) 179

R. Sporken, P.A. Thiry, P. Xhonneux, R. Caudano and J.P. Delrue, Spectroscopic study of metal/semimetal and metal/semiconductor interfaces 41/42 (1989) 201

R.T. Tung and F. Schrey, Epitaxial $CoSi_2$/Si(111) interfaces 41/42 (1989) 223

K. Akimoto, J. Mizuki, I. Hirosawa and J. Matsui, Interfacial superstructures studied by grazing incidence X-ray diffraction 41/42 (1989) 317
H. Akatsu and I. Ohdomari, HRTEM observation of the Si/SiO_2 interface 41/42 (1989) 357
K. Yokota, K. Ohtsuki, M. Ochi, S. Ishihara and I. Kimura, Accumulation of implanted arsenic at the interface during annealing on thermally oxidized Si and SiO_2 covered Si 41/42 (1989) 411
T. Hattori, H. Yamagishi, N. Koike, K. Imai and K. Yamabe, Structural studies of ultrathin silicon oxides and their interfaces by XPS 41/42 (1989) 416
P.S. Ho, Chemistry and adhesion of metal–polymer interfaces 41/42 (1989) 559
Y. Hatanaka, K. Mitsuoka and T. Yamaguchi, Properties of a-Si:H based interface transient layers measured by in-situ ellipsometry 41/42 (1989) 591

Ion bombardment

F. Priolo, A. La Ferla, C. Spinella, E. Rimini, S.U. Campisano and G. Ferla, Crystal–amorphous-silicon interface kinetics under ion beam irradiation 41/42 (1989) 619

Ion implantation

K. Yokota, K. Ohtsuki, M. Ochi, S. Ishihara and I. Kimura, Accumulation of implanted arsenic at the interface during annealing on thermally oxidized Si and SiO_2 covered Si 41/42 (1989) 411

Ion scattering

R.S. Williams, R.S. Daley, J.H. Huang and R.M. Charatan, Initial stages of metal/semiconductor interface formation: Au and Ag on Si(111) 41/42 (1989) 70
K. Sumitomo, K. Tanaka, Y. Izawa, I. Katayama, F. Shoji, K. Oura and T. Hanawa, Structural study of Ag overlayers deposited on a Si(111) substrate by impact-collision ion-scattering-spectroscopy with time-of-flight detection 41/42 (1989) 112
M. Renda and K. Morita, Epitaxial growth of a mono-crystalline metastable AuIn layer at the Au/InP(001) interface 41/42 (1989) 216
M. Itoh, M. Kinoshita, T. Ajioka, M. Itoh and T. Inada, Crystalline quality of heteroepitaxial silicon on epitaxial $NiSi_2/Si(100)$ 41/42 (1989) 262
K. Suguro, Y. Nakasaki, T. Yoshii and T. Itoh, Barrier metal between tungsten and silicon for high temperature processing 41/42 (1989) 277
T. Ito, A. Yamama, A. Hiraki and M. Satou, Silicidation of porous silicon and its application for the fabrication of a buried metal layer 41/42 (1989) 301
H. Hasegawa, H. Ohno, H. Ishii, T. Haga, Y. Abe and H. Takahashi, Origin and properties of interface states at insulator–semiconductor and semiconductor–semiconductor interfaces of compound semiconductors 41/42 (1989) 372
A.S. Barrière, G. Couturier, H. Guegan, T. Séguelong, A. Thabti, P. Alnot and J. Chazelas, Interface GaAs – gallium fluoride thin film grown by fluorination. Electrical behaviour of the obtained MIS fluorinated GaAs structures 41/42 (1989) 383
S. Tatarenko, J. Cibert, Y. Gobil, G. Feuillet, K. Saminadayar, A.C. Chami and E. Ligeon, RHEED, XPS, HRTEM and channeling studies of molecular beam epitaxy growth of CdTe on (001) GaAs 41/42 (1989) 470
H.C. Lee, H. Ishiwara, S. Furukawa, K. Saiki and A. Koma, Distribution of interfacial As atoms in the electron-beam exposure and epitaxy (EBE-epitaxy) technique for growing GaAs films on $CaF_2/Si(111)$ structures 41/42 (1989) 553
T. Wada, M. Takeda, T. Yamada and M. Ichimura, Formation of a Ge_xSi_{1-x} alloy layer by high-energy electron-beam irradiation 41/42 (1989) 580
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F. Priolo, A. La Ferla, C. Spinella, E. Rimini, S.U. Campisano and G. Ferla, Crystal–amorphous-silicon interface kinetics under ion beam irradiation 41/42 (1989) 619

Iron

Y. Kamiura, F. Hashimoto and M. Iwami, Iron accumulation at the $Si–SiO_2$ interface and possible reduction of SiO_2 41/42 (1989) 447

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G. Le Lay, K. Hricovini and J.E. Bonnet, Synchrotron radiation investigation and surface spectroscopy studies of prototypical systems: lead–semiconductor interfaces 41/42 (1989) 25

Light scattering

N. Esser, M. Hünermann, U. Resch, D. Spaltmann, J. Geurts, D.R.T. Zahn, W. Richter and R.H. Williams, Bismuth on GaAs(110): characterisation of growth mode and Schottky barrier formation at low and room temperature 41/42 (1989) 169

Y. Borensztein, T. Lopez-Rios and G. Vuye, Roughness induced at Si(111) surfaces by high temperature heating 41/42 (1989) 439

F. Priolo, A. La Ferla, C. Spinella, E. Rimini, S.U. Campisano and G. Ferla, Crystal–amorphous-silicon interface kinetics under ion beam irradiation 41/42 (1989) 619

Luminescence

J. Christen, M. Grundmann and D. Bimberg, Direct imaging and theoretical modelling of the atomistic morphological and chemical structure of semiconductor heterointerfaces 41/42 (1989) 329

C. López, J. Sánchez-Dehesa, F. Meseguer, F. Borondo and K. Ploog, Electronic structure of modulation n-doped multiple quantum well 41/42 (1989) 464

T. Sasaki, T. Matsuoka and A. Katsui, MOVPE-grown GaN on polar planes of 6H-SiC 41/42 (1989) 504

S. Hongo, Y. Kataoka, T. Urano and T. Kanaji, Evaluation by resonant light scattering of ZnTe epitaxial layer deposited on GaAs 41/42 (1989) 522

K. Kanamoto, K. Fujiwara, Y. Tokuda, N. Tsukada, M. Ishii and T. Nakayama, Photoluminescence line shape due to arrayed steps at the interfaces of GaAs/AlGaAs single quantum wells grown on vicinal surfaces by molecular beam epitaxy 41/42 (1989) 526

S. Hayashi, T. Sakamoto, S. Fujita and S. Fujita, Strained-layer superlattice buffers for high-quality heteroepilayers of ZnSe on GaAs 41/42 (1989) 534

H. Okumura, K. Miki, K. Sakamoto, T. Sakamoto, K. Endo and S. Yoshida, Raman scattering and photoluminescence characterization of Ge/Si strained-layer superlattices grown by phase-locked epitaxy 41/42 (1989) 548

Metal–semiconductor interfaces

W.E. Spicer, R. Cao, K. Miyano, T. Kendelewicz, I. Lindau, E. Weber, Z. Liliental-Weber and N. Newman, From synchrotron radiation to I–V measurements of GaAs Schottky barrier formation 41/42 (1989) 1

D. Paget, H.-J. Drouhin and J. Peretti, Infrared field assisted photoemission of metal–semiconductor structures 41/42 (1989) 38

A. Ichimiya, S. Kohmoto, T. Fujii and Y. Horio, RHEED intensity analysis of Si(111)$\sqrt{3} \times \sqrt{3}$-Ag structure 41/42 (1989) 82

F. Salvan, F. Thibaudau and Ph. Dumas, STM studies of metal–semiconductor interface formation 41/42 (1989) 88

M. Iwami, M. Kusaka, M. Hirai, M. Kubota, H. Tochihara and Y. Murata, Mechanism of alloy formation due to noble metal deposition on silicon surfaces at room temperature: chemical bonding model 41/42 (1989) 97

T. Urano, M. Kaburagi, S. Hongo and T. Kanaji, LEED I–V curve analysis for the structure of iron films on Si(111) surfaces 41/42 (1989) 103

K. Sumitomo, K. Tanaka, Y. Izawa, I. Katayama, F. Shoji, K. Oura and T. Hanawa, Structural study of Ag overlayers deposited on a Si(111) substrate by impact-collision ion-scattering-spectroscopy with time-of-flight detection 41/42 (1989) 112

S.-T. Li, S. Hasegawa, N. Yamashita and H. Nakashima, Initial stages of aluminum epitaxy on the Si(111)-$\sqrt{3} \times \sqrt{3}$-Al surface studied by electron-energy-loss spectroscopy 41/42 (1989) 118

K. Hirose, H. Tsuda and T. Mizutani, Control of the Al/GaAs Schottky barrier height using a rare-earth metal interlayer 41/42 (1989) 174

Y. Gekka, M. Saitoh, K. Ohga, Y. Akaida and M. Akimoto, Electrical characteristics of metal contacts on the surfaces of a-Si:H films annealed at low temperature 41/42 (1989) 184

R.H. Williams, N. Forsyth, I.M. Dharmadasa and Z. Sobiesierski, Metal contacts to II–VI semiconductors: CdS and CdTe 41/42 (1989) 189
M. Murakami, H.J. Kim, Y.-C. Shih, W.H. Price and C.C. Parks, Effects of interfacial microstructure on ohmic contacts to GaAs 41/42 (1989) 195
R. Sporken, P.A. Thiry, P. Xhonneux, R. Caudano and J.P. Delrue, Spectroscopic study of metal/semimetal and metal/semiconductor interfaces 41/42 (1989) 201
H. Sugahara and J. Nagano, Thermal stability of WSiN–GaAs and Au–WSiN interfaces 41/42 (1989) 207
M. Renda and K. Morita, Epitaxial growth of a mono-crystalline metastable AuIn layer at the Au/InP(001) interface 41/42 (1989) 216
P.J. van den Hoek and E.J. Baerends, Chemical bonding at metal–semiconductor interfaces 41/42 (1989) 236
I. Yamada, Interfacial structure of ICB epitaxially deposited Al(110) bicrystal films on Si(100) substrates 41/42 (1989) 253
K. Takayanagi, Y. Tanishiro, T. Ishitsuka and K. Akiyama, In-situ UHV electron microscope study of metal–silicon surfaces 41/42 (1989) 337
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A.S. Barrière, G. Couturier, H. Guegan, T. Séguelong, A. Thabti, P. Alnot and J. Chazelas, Interface GaAs – gallium fluoride thin film grown by fluorination. Electrical behaviour of the obtained MIS fluorinated GaAs structures 41/42 (1989) 383
Y. Yasuda, S. Zaima and M. Sakashita, Studies on charge trapping and interface state generation in MOS capacitors at low temperatures 41/42 (1989) 420
S. Zaima, T. Maruyama and Y. Yasuda, Piezoresistance in n-channel inversion layers of Si MOSFET's 41/42 (1989) 433
S. Fujieda, K. Akimoto, I. Hirosawa, Y. Mochizuki, J. Mizuki, Y. Matsumoto and J. Matsui, Electrical properties and structures of the MOCVD-AlN/GaAs interface 41/42 (1989) 516
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D.R.T. Zahn, W. Richter, T. Eickhoff, J. Geurts, T.D. Golding, J.H. Dinan, K.J. Mackey and R.H. Williams, The influence of Cd overpressure in the molecular beam epitaxy of InSb/CdTe heterostructures: a combined Raman and infrared spectroscopy study 41/42 (1989) 497
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S. Hongo, Y. Kataoka, T. Urano and T. Kanaji, Evaluation by resonant light scattering of ZnTe epitaxial layer deposited on GaAs 41/42 (1989) 522
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Y. Yamada Maruo, M. Oshima, T. Waho, T. Kawamura, S. Maeyama and T. Miyahara, Photoemission studies of bonding properties at the MBE-grown CaF_2/GaAs interface 41/42 (1989) 647

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H. Sugahara and J. Nagano, Thermal stability of WSiN–GaAs and Au–WSiN interfaces 41/42 (1989) 207
N. Fujimura and T. Ito, $TiSi_2$ formation at the Ti-rich TiN_x/Si interface 41/42 (1989) 272
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S. Fujieda, K. Akimoto, I. Hirosawa, Y. Mochizuki, J. Mizuki, Y. Matsumoto and J. Matsui, Electrical properties and structures of the MOCVD-AlN/GaAs interface 41/42 (1989) 516

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S. Hayashi, T. Sakamoto, S. Fujita and S. Fujita, Strained-layer superlattice buffers for high-quality heteroepilayers of ZnSe on GaAs 41/42 (1989) 534
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S. Nadahara, J. Shiozawa, K. Imai, K. Suguro and K. Yamabe, Protuberance growth at polysilicon surfaces during oxidation 41/42 (1989) 425
Y. Yasuda, S. Zaima, T. Kaida and Y. Koide, Formation of Si–SiO_2 interfaces at low temperatures using microwave-excited plasma 41/42 (1989) 429

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W.E. Spicer, R. Cao, K. Miyano, T. Kendelewicz, I. Lindau, E. Weber, Z. Liliental-Weber and N. Newman, From synchrotron radiation to *I–V* measurements of GaAs Schottky barrier formation 41/42 (1989) 1
G. Le Lay, K. Hricovini and J.E. Bonnet, Synchrotron radiation investigation and surface spectroscopy studies of prototypical systems: lead–semiconductor interfaces 41/42 (1989) 25
D. Paget, H.-J. Drouhin and J. Peretti, Infrared field assisted photoemission of metal–semiconductor structures 41/42 (1989) 38

S. Nakanishi, H. Tokutaka, K. Nishimori, S. Kishida and N. Ishihara, The difference between 6H-SiC (0001) and (000$\bar{1}$) faces observed by AES, LEED and ESCA 41/42 (1989) 44

S. Kono, Y. Enta, T. Abukawa, T. Kinoshita and T. Sakamoto, Photoelectron spectroscopy and photoelectron diffraction studies of Si(001)2 × 1-K and -Cs surfaces 41/42 (1989) 75

M. Iwami, M. Kusaka, M. Hirai, M. Kubota, H. Tochihara and Y. Murata, Mechanism of alloy formation due to noble metal deposition on silicon surfaces at room temperature: chemical bonding model 41/42 (1989) 97

X.M. Ding, G.S. Dong, X.K. Lu, H.Y. Xiao, P. Chen and X. Wang, Application of HREELS to Al/GaAs and Al/GaP interfaces 41/42 (1989) 123

D.W. Niles, M. Tang, J. McKinley, R. Zanoni and G. Margaritondo, From heterojunction interfaces to metal–semiconductor interfaces 41/42 (1989) 139

D.R.T. Zahn, W. Richter, A.B. McLean, R.H. Williams, C. Stephens, I.T. McGovern, R. Cimino, W. Braun and N. Esser, Temperature effects on the formation of the Sb/InP(110) interface 41/42 (1989) 179

R.H. Williams, N. Forsyth, I.M. Dharmadasa and Z. Sobiesierski, Metal contacts to II–VI semiconductors: CdS and CdTe 41/42 (1989) 189

H. Sugahara and J. Nagano, Thermal stability of WSiN–GaAs and Au–WSiN interfaces 41/42 (1989) 207

N. Cherief, R. Cinti, M. De Crescenzi, J. Derrien, T.A. Nguyen Tan and J.Y. Veuillen, Heteroepitaxy of metallic and semiconducting silicides on silicon 41/42 (1989) 241

L. Haderbache, P. Wetzel, C. Pirri, J.C. Peruchetti, D. Bolmont and G. Gewinner, Identification of three distinct $CoSi_2(111)(1 \times 1)$ surface structures 41/42 (1989) 257

T.A. Nguyen Tan, N. Guerfi, J.Y. Veuillen and J. Derrien, Oxidation of $TaSi_2$ thin films on polycrystalline Si 41/42 (1989) 266

N. Fujimura, S. Tachibana and T. Ito, Characterization of Si-rich WSi_x on Si 41/42 (1989) 286

J.F. Morar, U.O. Karlsson, R.I.G. Uhrberg, J. Kanski, P.O. Nilsson and H. Qu, Angle-resolved photoemission study of the As/Ge(100) interface 41/42 (1989) 312

F.J. Himpsel, T.F. Heinz, A.B. McLean and E. Palange, Bonding at silicon/insulator interfaces 41/42 (1989) 346

C.A. Sébenne, J.P. Lacharme, I. Andriamanantenasoa and M. Khial, Local roughness and surface states on Si(001): analysis of vacuum annealings and oxygen adsorption–desorption processes 41/42 (1989) 352

A. Ourmazd, P.H. Fuoss, J. Bevk and J.F. Morar, The $Si(001)/SiO_2$ interface 41/42 (1989) 365

A.S. Barrière, G. Couturier, H. Guegan, T. Séguelong, A. Thabti, P. Alnot and J. Chazelas, Interface GaAs – gallium fluoride thin film grown by fluorination. Electrical behaviour of the obtained MIS fluorinated GaAs structures 41/42 (1989) 383

H. Ishii, H. Hasegawa, A. Ishii and H. Ohno, X-ray photo-electron spectroscopy analysis of InP insulator–semiconductor structures prepared by anodic oxidation 41/42 (1989) 390

P. Soukiassian, H.I. Starnberg and T. Kendelewicz, Insulator–semiconductor interface formation by electronic promotion using alkali metal and removal of the catalyst 41/42 (1989) 395

T. Hattori, H. Yamagishi, N. Koike, K. Imai and K. Yamabe, Structural studies of ultrathin silicon oxides and their interfaces by XPS 41/42 (1989) 416

S. Tatarenko, J. Cibert, Y. Gobil, G. Feuillet, K. Saminadayar, A.C. Chami and E. Ligeon, RHEED, XPS, HRTEM and channeling studies of molecular beam epitaxy growth of CdTe on (001) GaAs 41/42 (1989) 470

R. Haight and J.A. Silberman, Surface intervalley scattering on GaAs(110) studied with picosecond laser photoemission 41/42 (1989) 487

B.A. Orlowski, J.P. Lacharme, C.A. Sébenne and S. Bensalah, Interface formation on n- and p-CdTe(110) surfaces with Cu and Au 41/42 (1989) 491

T. Sasaki, T. Matsuoka and A. Katsui, MOVPE-grown GaN on polar planes of 6H-SiC 41/42 (1989) 504

C. Tatsuyama, T. Tanbo and N. Nakayama, Heteroepitaxy between layered semiconductors GaSe and InSe 41/42 (1989) 539

P.S. Ho, Chemistry and adhesion of metal–polymer interfaces 41/42 (1989) 559

K. Maehashi, S. Hasegawa and H. Nakashima, Atomic rearrangement during the initial stages of GaAs growth on $Si(111)(\sqrt{3} \times \sqrt{3})$–Ga surface 41/42 (1989) 567

T. Aoyama, T. Sugi and T. Ito, Determination of band line-up in β-SiC/Si heterojunction for Si-HBT's 41/42 (1989) 584

Y. Yamada Maruo, M. Oshima, T. Waho, T. Kawamura, S. Maeyama and T. Miyahara, Photoemission studies of bonding properties at the MBE-grown CaF_2/GaAs interface 41/42 (1989) 647

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S. Zaima, T. Maruyama and Y. Yasuda, Piezoresistance in n-channel inversion layers of Si MOSFET's 41/42 (1989) 433

Plasma processing

Y. Gekka, M. Saitoh, K. Ohga, Y. Akaida and M. Akimoto, Electrical characteristics of metal contacts on the surfaces of a-Si:H films annealed at low temperature 41/42 (1989) 184

Y. Yasuda, S. Zaima, T. Kaida and Y. Koide, Formation of Si–SiO_2 interfaces at low temperatures using microwave-excited plasma 41/42 (1989) 429

K. Kamimura, Y. Takase, Y. Onuma and A. Kunioka, Surface nitridation of InP with a N_2 plasma 41/42 (1989) 443

J.-S. Ma, H. Kawarada, T. Yonehara, J.-I. Suzuki, J. Wei, Y. Yokota, H. Mori, H. Fujita and A. Hiraki, Interfacial structures and selective growth of diamond particles formed by plasma-assisted CVD 41/42 (1989) 572

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P.S. Ho, Chemistry and adhesion of metal–polymer interfaces 41/42 (1989) 559

Raman scattering

N. Esser, M. Hünermann, U. Resch, D. Spaltmann, J. Geurts, D.R.T. Zahn, W. Richter and R.H. Williams, Bismuth on GaAs(110): characterisation of growth mode and Schottky barrier formation at low and room temperature 41/42 (1989) 169

M. Yano, M. Ashida, Y. Iwai and M. Inoue, Characteristic properties of III–V_A/III–V_B heterointerfaces grown by molecular beam epitaxy 41/42 (1989) 457

C. López, J. Sánchez-Dehesa, F. Meseguer, F. Borondo and K. Ploog, Electronic structure of modulation n-doped multiple quantum well 41/42 (1989) 464

D.R.T. Zahn, W. Richter, T. Eickhoff, J. Geurts, T.D. Golding, J.H. Dinan, K.J. Mackey and R.H. Williams, The influence of Cd overpressure in the molecular beam epitaxy of InSb/CdTe heterostructures: a combined Raman and infrared spectroscopy study 41/42 (1989) 497

S. Hongo, Y. Kataoka, T. Urano and T. Kanaji, Evaluation by resonant light scattering of ZnTe epitaxial layer deposited on GaAs 41/42 (1989) 522

T. Takeuchi, C. Maezawa, T. Nomura, K. Ishikawa, M. Miyao and M. Hagino, Raman study of strain distribution in interface region of GaAs/GaP heteroepitaxial layers grown by MBE 41/42 (1989) 530

H. Okumura, K. Miki, K. Sakamoto, T. Sakamoto, K. Endo and S. Yoshida, Raman scattering and photoluminescence characterization of Ge/Si strained-layer superlattices grown by phase-locked epitaxy 41/42 (1989) 548

K. Iizuka, T. Yoshida, M. Hasobe, I. Matsuda and T. Suzuki, Raman study of the stress in MBE-grown Al_x-$Ga_{1-x}As$ on Si 41/42 (1989) 587

Schottky barrier

W.E. Spicer, R. Cao, K. Miyano, T. Kendelewicz, I. Lindau, E. Weber, Z. Liliental-Weber and N. Newman, From synchrotron radiation to *I–V* measurements of GaAs Schottky barrier formation 41/42 (1989) 1

M.H. Hecht, L.D. Bell and W.J. Kaiser, Ballistic-electron-emission microscopy of subsurface defects at the Au–GaAs(100) interface 41/42 (1989) 17

W. Mönch, Mechanisms of barrier formation in Schottky contacts: metal-induced surface and interface states 41/42 (1989) 128

D.W. Niles, M. Tang, J. McKinley, R. Zanoni and G. Margaritondo, From heterojunction interfaces to metal–semiconductor interfaces 41/42 (1989) 139

F. Flores, A. Muñoz and J.C. Durán, Semiconductor interface formation: the role of the induced density of interface states 41/42 (1989) 144

R. Ludeke, A. Taleb-Ibrahimi and G. Jezequel, Delocalization of defects: a new model for the Schottky barrier 41/42 (1989) 151

J.H. Werner, H. von Känel, G. Markewitz and R.T. Tung, Pressure dependences of silicide/silicon Schottky barrier heights 41/42 (1989) 159

H. Fujitani and S. Asano, Electronic structure of Si/disilicide interfaces 41/42 (1989) 164
N. Esser, M. Hünermann, U. Resch, D. Spaltmann, J. Geurts, D.R.T. Zahn, W. Richter and R.H. Williams, Bismuth on GaAs(110): characterisation of growth mode and Schottky barrier formation at low and room temperature 41/42 (1989) 169
K. Hirose, H. Tsuda and T. Mizutani, Control of the Al/GaAs Schottky barrier height using a rare-earth metal interlayer 41/42 (1989) 174
Y. Gekka, M. Saitoh, K. Ohga, Y. Akaida and M. Akimoto, Electrical characteristics of metal contacts on the surfaces of a-Si:H films annealed at low temperature 41/42 (1989) 184
R.H. Williams, N. Forsyth, I.M. Dharmadasa and Z. Sobiesierski, Metal contacts to II–VI semiconductors: CdS and CdTe 41/42 (1989) 189
H. Sugahara and J. Nagano, Thermal stability of WSiN–GaAs and Au–WSiN interfaces 41/42 (1989) 207

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M. Murakami, H.J. Kim, Y.-C. Shih, W.H. Price and C.C. Parks, Effects of interfacial microstructure on ohmic contacts to GaAs 41/42 (1989) 195
H. Sugahara and J. Nagano, Thermal stability of WSiN–GaAs and Au–WSiN interfaces 41/42 (1989) 207
S. Ogawa, T. Yoshida, T. Kouzaki, S. Okuda and K. Tsukamoto, Thermal instability of the $TiSi_2$/Si structure: impurity effects 41/42 (1989) 290
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M. Yano, M. Ashida, Y. Iwai and M. Inoue, Characteristic properties of III–V_A/III–V_B heterointerfaces grown by molecular beam epitaxy 41/42 (1989) 457
S. Tatarenko, J. Cibert, Y. Gobil, G. Feuillet, K. Saminadayar, A.C. Chami and E. Ligeon, RHEED, XPS, HRTEM and channeling studies of molecular beam epitaxy growth of CdTe on (001) GaAs 41/42 (1989) 470
S. Goto, H. Kakibayashi, M. Kawata and T. Usagawa, Evaluation of disordering at low doping concentration in selectively Si-doped $Al_{0.3}Ga_{0.7}As$/GaAs heterointerfaces 41/42 (1989) 480
D.R.T. Zahn, W. Richter, T. Eickhoff, J. Geurts, T.D. Golding, J.H. Dinan, K.J. Mackey and R.H. Williams, The influence of Cd overpressure in the molecular beam epitaxy of InSb/CdTe heterostructures: a combined Raman and infrared spectroscopy study 41/42 (1989) 497
S.K. De Figueiredo and A.C. Ferraz, Interface geometry of $(GaAs)_n(InAs)_n$ and $(GaP)_n(InP)_n$ ultra-thin superlattices 41/42 (1989) 509
T. Nomura, K. Wakatuki, M. Miyao and M. Hagino, Characterization of the GaAs buffer layer grown on GaP by MBE for the two-step growth method 41/42 (1989) 512
S. Hongo, Y. Kataoka, T. Urano and T. Kanaji, Evaluation by resonant light scattering of ZnTe epitaxial layer deposited on GaAs 41/42 (1989) 522
K. Kanamoto, K. Fujiwara, Y. Tokuda, N. Tsukada, M. Ishii and T. Nakayama, Photoluminescence line shape due to arrayed steps at the interfaces of GaAs/AlGaAs single quantum wells grown on vicinal surfaces by molecular beam epitaxy 41/42 (1989) 526
T. Aoyama, T. Sugi and T. Ito, Determination of band line-up in β-SiC/Si heterojunction for Si-HBT's 41/42 (1989) 584
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R.T. Tung and F. Schrey, Epitaxial $CoSi_2$/Si(111) interfaces 41/42 (1989) 223

J. Falta, M. Horn and M. Henzler, SPA-LEED studies of defects in thin epitaxial $NiSi_2$ layers on Si(111) 41/42 (1989) 230

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N. Cherief, R. Cinti, M. De Crescenzi, J. Derrien, T.A. Nguyen Tan and J.Y. Veuillen, Heteroepitaxy of metallic and semiconducting silicides on silicon 41/42 (1989) 241

L. Haderbache, P. Wetzel, C. Pirri, J.C. Peruchetti, D. Bolmont and G. Gewinner, Identification of three distinct $CoSi_2(111)(1 \times 1)$ surface structures 41/42 (1989) 257

M. Itoh, M. Kinoshita, T. Ajioka, M. Itoh and T. Inada, Crystalline quality of heteroepitaxial silicon on epitaxial $NiSi_2$/Si(100) 41/42 (1989) 262

T.A. Nguyen Tan, N. Guerfi, J.Y. Veuillen and J. Derrien, Oxidation of $TaSi_2$ thin films on polycrystalline Si 41/42 (1989) 266

N. Fujimura and T. Ito, $TiSi_2$ formation at the Ti-rich TiN_x/Si interface 41/42 (1989) 272

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N. Fujimura, S. Tachibana and T. Ito, Characterization of Si-rich WSi_x on Si 41/42 (1989) 286

S. Ogawa, T. Yoshida, T. Kouzaki, S. Okuda and K. Tsukamoto, Thermal instability of the $TiSi_2$/Si structure: impurity effects 41/42 (1989) 290

Y. Kawadzu, M. Iioka, A. Fujii, H. Oyanagi and T. Arai, Interfacial reaction of nickel/hydrogenated amorphous silicon system at low temperature studied by fluorescence EXAFS 41/42 (1989) 296

T. Ito, A. Yamama, A. Hiraki and M. Satou, Silicidation of porous silicon and its application for the fabrication of a buried metal layer 41/42 (1989) 301

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E. Vlieg and J.F. van der Veen, X-ray scattering studies of semiconductor interfaces: atomic structure and morphology 41/42 (1989) 62

R.S. Williams, R.S. Daley, J.H. Huang and R.M. Charatan, Initial stages of metal/semiconductor interface formation: Au and Ag on Si(111) 41/42 (1989) 70

S. Kono, Y. Enta, T. Abukawa, T. Kinoshita and T. Sakamoto, Photoelectron spectroscopy and photoelectron diffraction studies of Si(001)2 × 1-K and -Cs surfaces 41/42 (1989) 75

S. Kohmoto, S. Mizuno and A. Ichimiya, RHEED intensity analysis of Li/Si(111) structures 41/42 (1989) 107

M. Itoh, M. Kinoshita, T. Ajioka, M. Itoh and T. Inada, Crystalline quality of heteroepitaxial silicon on epitaxial $NiSi_2$/Si(100) 41/42 (1989) 262

A. Förster, J.M. Layet and H. Lüth, Evaluation of dopant profiles and diffusion constants by means of electron energy loss spectroscopy 41/42 (1989) 306

C.A. Sébenne, J.P. Lacharme, I. Andriamanantenasoa and M. Khial, Local roughness and surface states on Si(001): analysis of vacuum annealings and oxygen adsorption–desorption processes 41/42 (1989) 352

Y. Borensztein, T. Lopez-Rios and G. Vuye, Roughness induced at Si(111) surfaces by high temperature heating 41/42 (1989) 439

Y. Hatanaka, K. Mitsuoka and T. Yamaguchi, Properties of a-Si:H based interface transient layers measured by in-situ ellipsometry 41/42 (1989) 591

F. Priolo, A. La Ferla, C. Spinella, E. Rimini, S.U. Campisano and G. Ferla, Crystal–amorphous-silicon interface kinetics under ion beam irradiation 41/42 (1989) 619

K. Furukawa and A. Nakagawa, Applications of the silicon wafer direct-bonding technique to electron devices 41/42 (1989) 627

M. Okuyama, N. Fujiki, Y. Nakatani, K. Inoue and Y. Hamakawa, Growth behavior of highly oriented Si films on fused quartz by photo-CVD 41/42 (1989) 633

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S. Nakanishi, H. Tokutaka, K. Nishimori, S. Kishida and N. Ishihara, The difference between 6H-SiC (0001) and (000$\bar{1}$) faces observed by AES, LEED and ESCA 41/42 (1989) 44

K. Nishimori, H. Tokutaka, Z. Okinaga, S. Kishida and N. Ishihara, Observation of Si and SiC surface structures using the magnetic LEED method 41/42 (1989) 49

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K. Yokota, K. Ohtsuki, M. Ochi, S. Ishihara and I. Kimura, Accumulation of implanted arsenic at the interface during annealing on thermally oxidized Si and SiO_2 covered Si 41/42 (1989) 411

T. Hattori, H. Yamagishi, N. Koike, K. Imai and K. Yamabe, Structural studies of ultrathin silicon oxides and their interfaces by XPS 41/42 (1989) 416

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Y. Yasuda, S. Zaima, T. Kaida and Y. Koide, Formation of Si–SiO_2 interfaces at low temperatures using microwave-excited plasma 41/42 (1989) 429

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S.K. De Figueiredo and A.C. Ferraz, Interface geometry of $(GaAs)_n(InAs)_n$ and $(GaP)_n(InP)_n$ ultra-thin superlattices 41/42 (1989) 509

S. Hayashi, T. Sakamoto, S. Fujita and S. Fujita, Strained-layer superlattice buffers for high-quality heteroepilayers of ZnSe on GaAs 41/42 (1989) 534

H. Okumura, K. Miki, K. Sakamoto, T. Sakamoto, K. Endo and S. Yoshida, Raman scattering and photoluminescence characterization of Ge/Si strained-layer superlattices grown by phase-locked epitaxy 41/42 (1989) 548

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S. Nadahara, J. Shiozawa, K. Imai, K. Suguro and K. Yamabe, Protuberance growth at polysilicon surfaces during oxidation 41/42 (1989) 425

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J. Falta, M. Horn and M. Henzler, SPA-LEED studies of defects in thin epitaxial $NiSi_2$ layers on Si(111) 41/42 (1989) 230
C.A. Sébenne, J.P. Lacharme, I. Andriamanantenasoa and M. Khial, Local roughness and surface states on Si(001): analysis of vacuum annealings and oxygen adsorption–desorption processes 41/42 (1989) 352
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F.J. Himpsel, T.F. Heinz, A.B. McLean and E. Palange, Bonding at silicon/insulator interfaces 41/42 (1989) 346
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H. Hasegawa, H. Ohno, H. Ishii, T. Haga, Y. Abe and H. Takahashi, Origin and properties of interface states at insulator–semiconductor and semiconductor–semiconductor interfaces of compound semiconductors 41/42 (1989) 372
T. Saitoh, H. Hasegawa, S. Konishi and H. Ohno, A computer simulation of the recombination process at compound semiconductor surfaces and hetero-interfaces 41/42 (1989) 402
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S. Kono, Y. Enta, T. Abukawa, T. Kinoshita and T. Sakamoto, Photoelectron spectroscopy and photoelectron diffraction studies of $Si(001)2 \times$ 1-K and -Cs surfaces 41/42 (1989) 75
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J.F. Morar, U.O. Karlsson, R.I.G. Uhrberg, J. Kanski, P.O. Nilsson and H. Qu, Angle-resolved photoemission study of the As/Ge(100) interface 41/42 (1989) 312
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E. Vlieg and J.F. van der Veen, X-ray scattering studies of semiconductor interfaces: atomic structure and morphology 41/42 (1989) 62

M. Renda and K. Morita, Epitaxial growth of a mono-crystalline metastable AuIn layer at the Au/InP(001) interface 41/42 (1989) 216

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T. Wada, M. Takeda, T. Yamada and M. Ichimura, Formation of a Ge_xSi_{1-x} alloy layer by high-energy electron-beam irradiation 41/42 (1989) 580

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M. Iwami, M. Kusaka, M. Hirai and H. Nakamura, A new non-destructive analysis of semiconductor heterojunctions with very thin surface layers: an application of soft X-ray spectroscopy to Si-compound (film)/Si (substrate) 41/42 (1989) 57

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